



Associate Professor

YOSHIDA Toshiyuki

Room 811, Interdisciplinary Faculty of Science and Engineering 3

TEL: 0852-32-6346 (Ext. 6314)

Email: yosisi[at]riko.shimane-u.ac.jp

(Please change [at] to @ for email.)

Website: http://www.ecs.shimane-u.ac.jp/~yosisi/index_E.html

Background

- 2019 Associate Professor, Department of Physics and Materials Science, Interdisciplinary Faculty of Science and Engineering (IFSE), Shimane University
- 2018 Assistant Professor, Dept. of Physics and Material Science, IFSE, Shimane University
- 2012 Assistant Professor, Dept. of Mechanical, Electrical and Electronic Engineering, IFSE, Shimane University
- 2007 Assistant Professor, Dept. of Electronic Control Systems Engineering, IFSE, Shimane University
- 2001 Research Associate, Dept. of Electronic Control Systems Engineering, IFSE, Shimane University
- 2001 Graduated the doctor's program, Graduate school of Electronics and Information Engineering, Hokkaido University
- 2000 Research Fellowship for Young Scientists, Japan Society for the Promotion of Science

Research

Characterization and Device Application of Surfaces and Interfaces in Semiconductor Thin-Films and Particle-Layers

Key papers

1. Toshiyuki Yoshida, Islam Md Maruf, and Yasuhisa Fujita: "Trial of Ga-doping on ZnO Nanoparticles by Thermal Treatment with Ga₂O₃ Nanoparticles", e-Journal of Surface Science and Nanotechnology, **18** (2020) pp.12-17.
2. Itohara Daiki, Kazato Shinohara, Toshiyuki Yoshida, and Yasuhisa Fujita: "P-channel and n-channel thin-film-transistor operation on sprayed ZnO nanoparticle layers", Journal of Nanomaterials, **2016** (2016) pp.8219326_1-6.
3. Toshiyuki Yoshida, and Tamotsu Hashizume: "Studies on atomic layer deposition Al₂O₃/In_{0.53}Ga_{0.47}As interface formation mechanism based on air-gap capacitance-voltage method", Applied Physics Letters, **101** (2012) pp.122102_1-4.
4. Toshiyuki Yoshida, Yoshiki Ebiko, Michiko Takei, Nobuo Sasaki, and Toshiaki Tsuchiya: "Grain-Boundary Related Hot Carrier Degradation Mechanism in Low-Temperature Polycrystalline Silicon Thin-Film Transistors", Japanese Journal of Applied Physics, Part 1, **42** 4B (2003) pp. 1999-2003.